

General Description(产品描述)

SE82XX series is designed for powersensitive applications. It includes a precision and high voltage input stage, an ultra-lowpower bias current branch, and results in a ultra-low-power and low-dropout linear regulator.

The SE82XX operates from an input voltage of $V_{OUT}+1V$ to 33V, consumes only 2.5 μ A of quiescent current, and offers 1% initial accuracy and low dropout voltage, 300mV typical at 100mA.

SE82XX provides fixed 3.0V, 3.3V and 5V outputs.

Other features include short-circuit protection and thermal shutdown.

Features(产品特性)

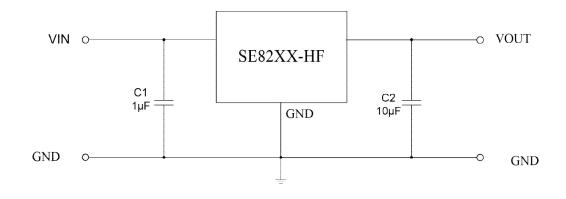
- Ultra Low Quiescent Current: 2µA(Typ.)
- Wide Operating Voltage: V_{OUT}+1V to 33V
- High output current: ≥200mA
- System startup with no overshoot
- Short circuit protection is designed with no overshoot
- UVLO 1.8V
- Low Dropout Voltage
- High Accuracy Output Voltage: ±1%
- Excellent power / load transient response
- Low temperature coefficient: ±100ppm/°C
- Thermal and Short-Circuit Protection
- SOT-89、SOT23-3、SOT23-5 packages
- Customer Pin Assignments are available

Applications(产品应用)

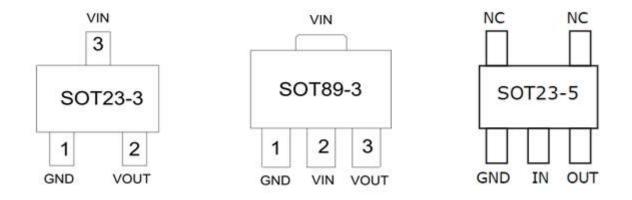
Battery-powered equipment
Smoke detector and sensor
Microcontroller Applications
Smart electric meter



Typical Application (典型应用电路)



Pin Configuration(管脚排列)

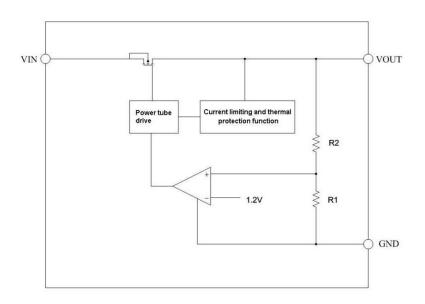


Pin Description (管脚功能描述)

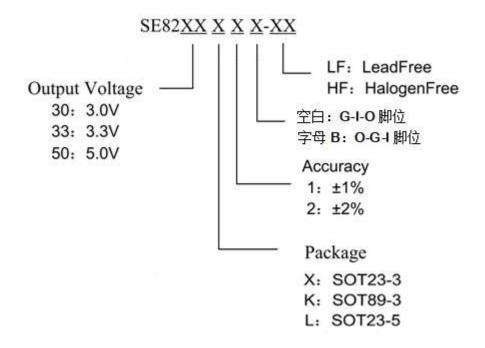
Pin Name	Pin Function Description			
VIN	In put pin			
VOUT	Out put pin			
GND	Ground pin			
NC	No connection			



Functional Block Diagram (功能框图)



Ordering Information(订货信息)





Absolute Maximum Ratings(最大额定参数)

Symbol	Parameter	Value	Units	
V _{IN}	Input Supply Voltage	35	V	
V _{OUT} GND	Output Voltage TO GND	15	\ \ \ \ \ \	
T _A	Operating Temperature	-40105		
T _{STG}	Storage Temperature	-40150	°c	
TJ	Maximum Junction Temperature	150		
T _{LEAD}	Lead Temperature (Soldering) 10 seconds	260		
		165(SOT89)		
θ_{JA}	Thermal Resistance, Junction-to-Ambient	280(SOT23-3)	°C/W	
	,	280(SOT23-5)		
		750(SOT89)		
P _D	Power Consumption	446(SOT23-3)	mW	
		446(SOT23-5)		
Electrostatic	Human Body Model (HBM)	4	kV	
discharge rating	Charged Device Model (MM)	100	V	

Note: Stresses exceeding the range specified under "Absolute Maximum Ratings" may cause substantial damage to the device. Functional operation of this device at other conditions beyond those listed in the specification is not implied and prolonged exposure to extreme conditions may affect device reliability.

Recommended Operating Conditions(推荐工作条件)

Symbol	Parameter	Maximum	Units
V _{IN}	Input Supply Voltage	33	V
T _A	Operating Temperature	-2085	°C
TLEAD	Lead Temperature (Soldering) 10 seconds	260	°C



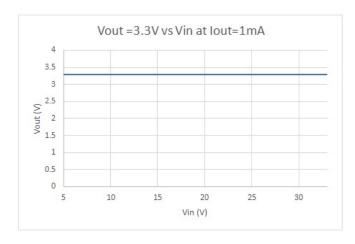
Electrical Characteristics(电气参数)

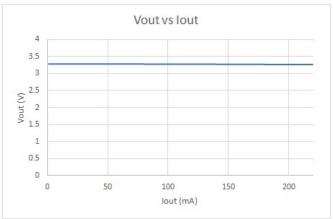
 $(TA=25^{\circ} C, CIN=1uF, VIN=VOUT+2.0V, COUT=10\mu F, unless otherwise noted)$

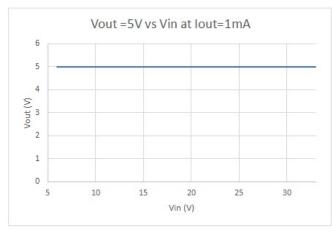
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IN}	Input Supply Voltage		2.8		33	٧
\/	Output Voltage Accuracy	I -10A	-1%		1%	٧
V _{OUT}		I _{OUT} =10mA	-2%		2%	٧
IQ	Quiescent Current	V _{IN} =12V,NO Load		2	3	μΑ
I _{OUT}	Output Current			200		mA
	Dropout Voltage	I _{OUT} =10mA ΔV _{OUT} = - V _{OUT} *2%		50		mV
V _{DROP}		I_{OUT} =100mA ΔV_{OUT} = - V_{OUT} *2%		500		mV
V_{LR}	Load Regulation	1mA≤l _{OUT} ≤150mA		40		mV
V_{SR}	Line Regulation	I_{OUT} =1mA, V_{IN} =(V_{OUT} +2V) to 24V		0.2		%/V
Ishort	Short Current			100		mA
T _{SHDN}	Thermal Protection			150		$^{\circ}\!$

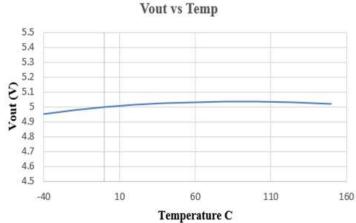


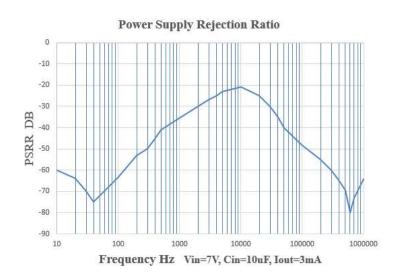
Typical Performance Characteristics







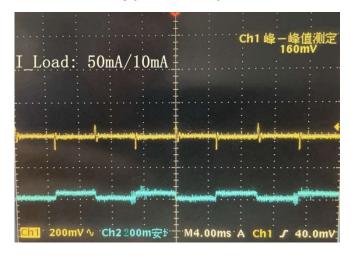




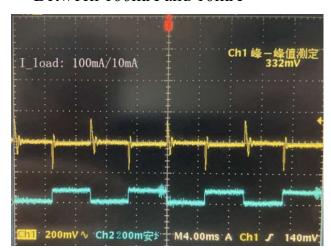


Transient Responses:

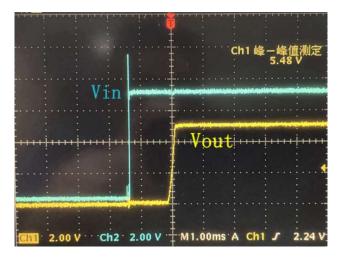
Between 50mA and 10mA



Between 100mA and 10mA

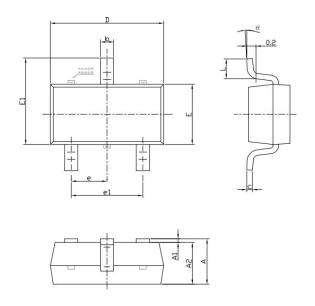


SoftStart Delay



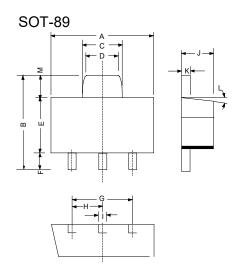


Outline Drawing for SOT-23-3



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Mln	Max	MIn	Max
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
е	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0"	8

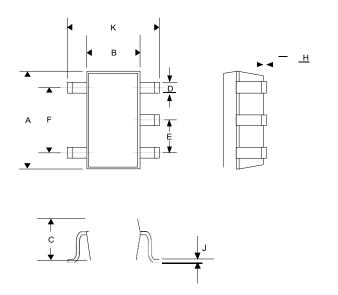
Outline Drawing for SOT-89



DIM ENSIONS					
DIA N	INCHES		ММ		
DIM ^N	M IN	M AX	M IN	M AX	
Α	0 .173	0 .181	4 .400	4 .600	
В	0 .159	0 .167	4 .050	4 .250	
С	0 .067	0 .075	1 .700	1 .900	
D	0 .051	0 .059	1 .300	1 .500	
Е	0 .094	0 .102	2 .400	2 .600	
F	0 .035	0 .047	0 .890	1 .200	
G	0 .118 R EF		3 .00 R EF		
Н	0 .059 R EF		1 .50 R EF		
I	0 .016	0 .020	0 .400	0 .520	
J	0 .055	0 .063	1 .400	1 .600	
K	0 .014	0 .016	0 .350	0 .410	
L	10 °TYP		10 °TYP		
М	0 .028 R EF		0 .70 R EF		



Outline Drawing for SOT-23-5



BUMENIONO					
DIMENSIONS					
DIM	INCHES		MM		
	MIN	MAX	MIN	MAX	
Α	0.110	0.120	2.80	3.05	
В	0.059	0.070	1.50	1.75	
С	0.036	0.051	0.90	1.30	
D	0.014	0.020	0.35	0.50	
E	-	0.037	-	0.95	
F	-	0.075	-	1.90	
Н	-	0.006	-	0.15	
J	0.0035	0.008	0.090	0.20	
K	0.102	0.118	2.60	3.00	

联系方式:

北京思旺电子技术有限公司-中国总部

地址:中国北京市海淀区信息路 22 号上地科技综合楼 B 座二层

邮编: 100085

电话: 010-82895700/1/5

传真: 010-82895706

邮箱: sales@seawardinc.com.cn

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Seaward Electronics Incorporated – 北美办事处

1512 Centre Pointe Dr. Milpitas,

CA95035, USA

电话: 1-650-444-0713